AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Serial Number: 08/984,560

Filing Date: December 3, 1997

Title: MEMORY DEVICE WITH PATTERNED AND PATTERNLESS ADDRESSING

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[sequence] a sequential column address access.

D3)

(Once Amended) A storage device, as in Claim 26, wherein the sequence column address access is selected from a group consisting of an interleaved column address access and a linear column address access.

Please add the following new claims:

13,62

(New) A storage device comprising:

control logic for selecting between a patternless addressing scheme and a patterned addressing scheme;

a counter; and

switching circuitry for switching between a first pathway and a second pathway depending on which of said patternless addressing scheme and said patterned addressing scheme is selected, wherein the first pathway and the second pathway are coupled to a temporary storage device for providing at least one external address to the switching circuitry, and wherein the counter is coupled to the temporary storage device to receive a selected portion of the external address for generating an internal address.

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(New) The storage device of Claim 62, wherein the internal address is provided to the temporary storage device through the switching circuitry

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64. (New) The storage device of Claim 62, wherein the patternless addressing scheme provides a pipelined extended data out pattern.

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65. (New) A storage device comprising:

control logic for selecting between a patternless addressing scheme and a patterned addressing scheme; and

switching circuitry for switching between a first pathway and a second pathway depending on which of said patternless addressing scheme and said patterned addressing scheme

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is selected, wherein the patternless addressing scheme provides a pipelined extended data out pattern.

(New) The storage device of Claim 65, wherein the patterned addressing scheme provides a burst extended data out pattern.

(New) The storage device of Claim 65, wherein the switching circuitry includes at least one multiplexed device.

54 68: (New) A storage device comprising:

control logic for selecting between a patternless addressing scheme and a patterned addressing scheme; and

switching circuitry for switching between a first pathway and a second pathway depending on which of said patternless addressing scheme and said patterned addressing scheme is selected, wherein the patterned addressing scheme provides a burst extended data out pattern.

(New) The storage device of Claim 68, wherein the switching circuitry includes at least one multiplexed device.

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70. (New) A memory device, comprising:

a memory array operable in a burst mode of operation or a pipelined mode of operation; control logic for selecting between the burst mode of operation or the pipelined mode of operation; and

switching circuitry for switching between a first, burst data pathway and a second, pipeline data pathway depending on which of the burst or pipelined modes of operation is selected, wherein the first pathway and the second pathway are coupled to a temporary storage device for providing at least one external address to the switching circuitry.

(New) The memory device of Claim 70, further comprising a counter coupled to the temporary storage device to receive a selected portion of the external address for generating an

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